



# MCH6616

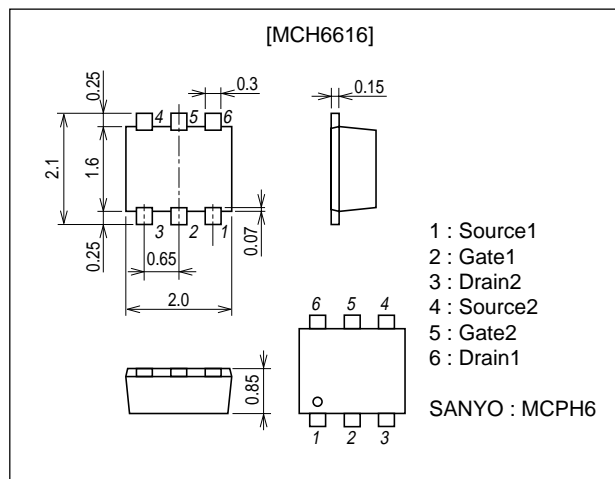
## Ultrahigh-Speed Switching Applications

### Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.
- Composite type with 2 MOSFETs contained in a single package, facilitating high-density mounting.

### Package Dimensions

unit : mm  
2173A



### Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		20	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		1.6	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	6.4	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm <sup>2</sup> ×0.8mm)1unit	0.8	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	20			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =0.8A	1.6	2.4		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =0.8A, V <sub>GS</sub> =4V		180	230	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =0.4A, V <sub>GS</sub> =2.5V		220	310	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =0.1A, V <sub>GS</sub> =1.8V		300	450	mΩ

Marking : FQ

Continued on next page.

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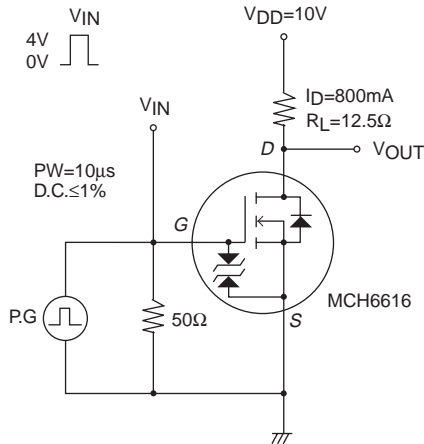
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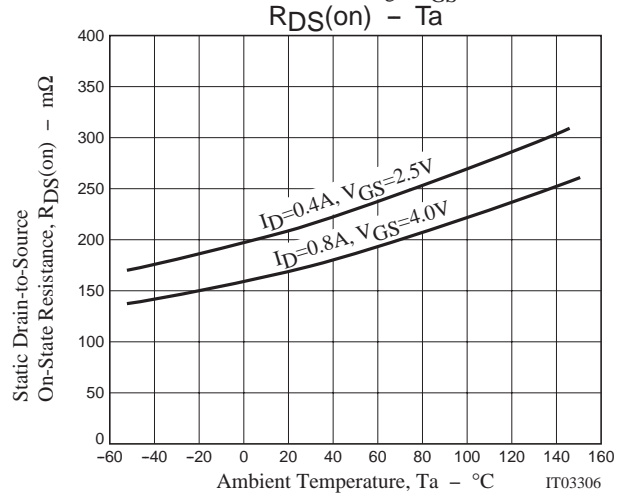
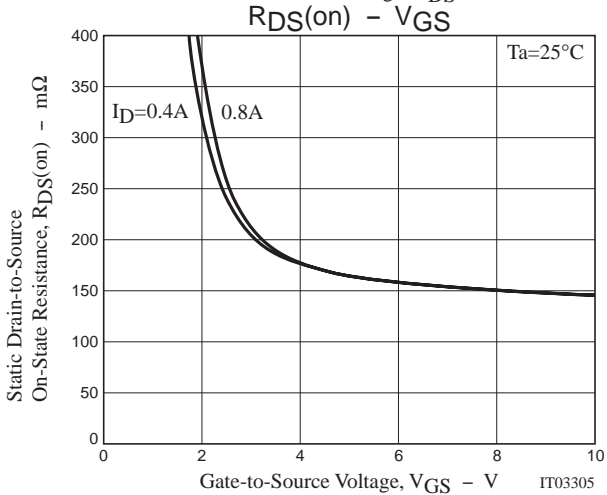
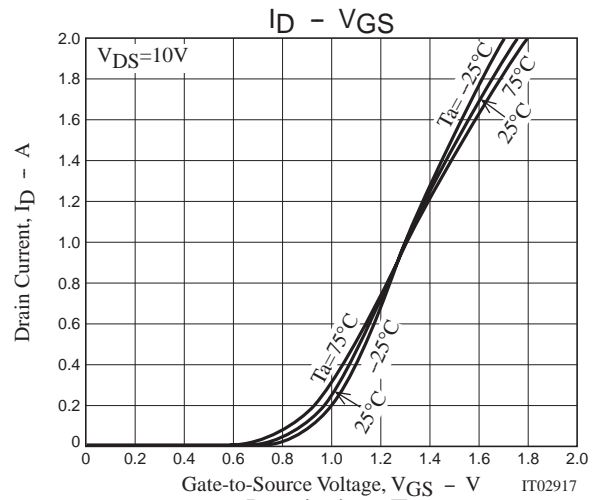
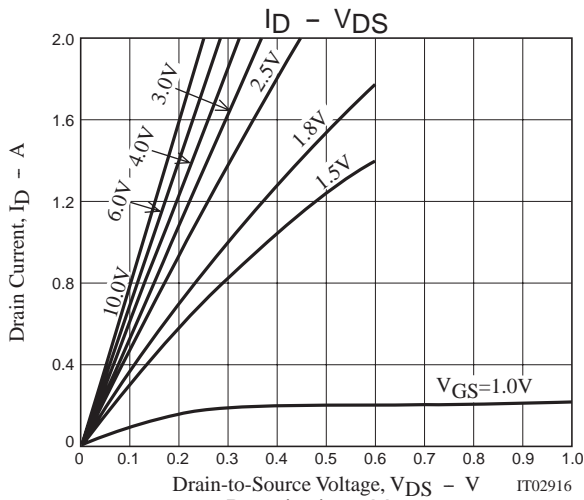
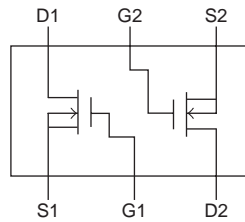
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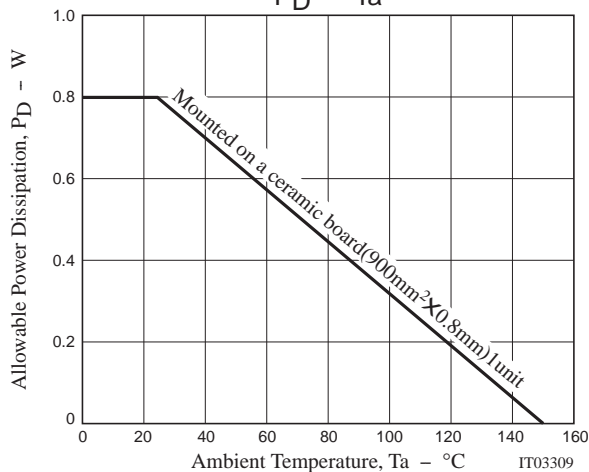
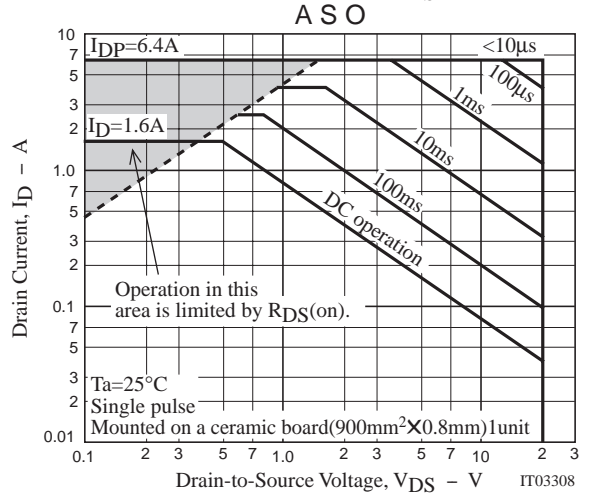
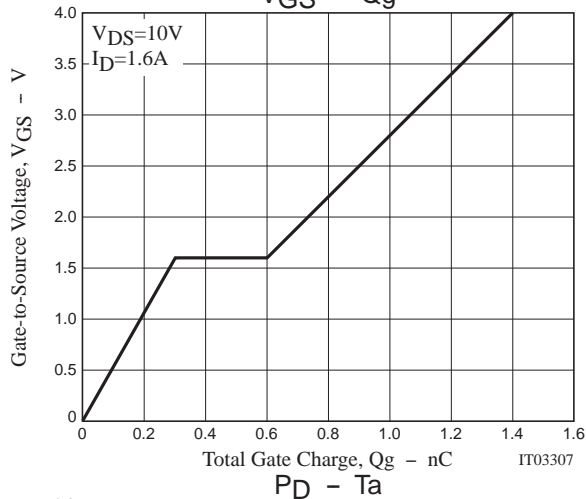
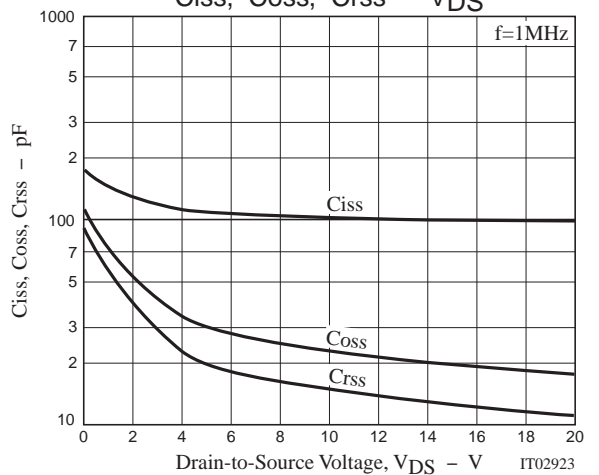
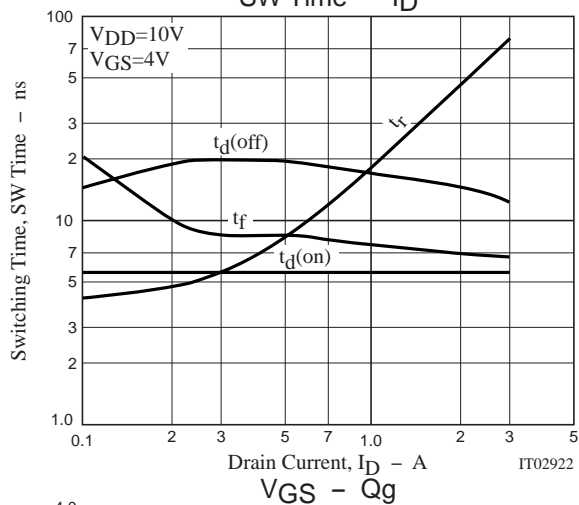
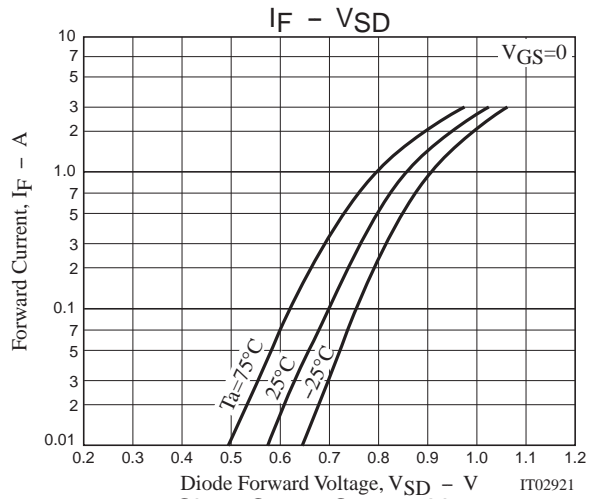
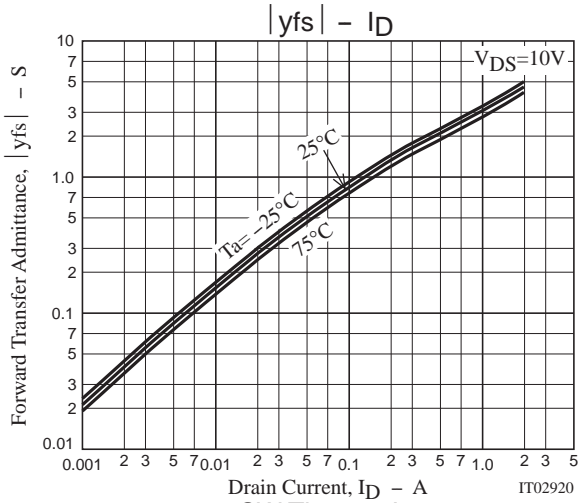
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		105		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		23		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		15		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit		6		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit		16		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit		19		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit		8		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =1.6A		1.4		nC
Gate-to-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =1.6A		0.3		nC
Gate-to-Drain "Miller" Charge	Q <sub>gd</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4V, I <sub>D</sub> =1.6A		0.3		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.6A, V <sub>GS</sub> =0		0.92	1.2	V

## Switching Time Test Circuit



## Electrical Connection





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